

Si3404 Data Sheet

Fully-Integrated IEEE 802.3 Type 1-Compliant POE PD Interface and High-Efficiency Switching Regulator with Compact Footprint

The Si3404 integrates all power management and control functions required in a Power-over-Ethernet (PoE) powered device (PD) application. These devices convert the high voltage supplied over the 10/100/1000BASE-T Ethernet connection to a regulated, low-voltage output supply. The optimized architecture of this device minimizes the solution footprint and external BOM cost and enables the use of low-cost external components while maintaining high performance. The Si3404 integrates a transient surge suppressor. The switching power FET and all associated functions are also integrated. The integrated, current mode controlled switching regulator supports isolated or nonisolated flyback and buck converter topologies. The switching frequency for the regulator is tunable with a simple external resistor value to help avoid unwanted harmonics for better emissions control.

This device fully supports the IEEE 802.3at specification for Type 1, single-event classification. Standard external resistors provide the proper IEEE 802.3 signatures for the detection function and programming of the classification mode, and internal startup circuits ensure well-controlled soft-start initial operation of both the hotswap switch and the voltage regulator.

The Si3404 is available in a low-profile, 20-pin, 4 x 4 mm QFN package.

KEY FEATURES

- Type 1 (PoE) power
- IEEE 802.3at Type 1 compliance
- Current mode dc-dc converter
- Tunable switching frequency
- Transformer bias winding support
- Auxiliary adapter support
- Integrated hotswap FET and switching FET
- 120 V Absolute Max voltage performance
- Extended –40 to +85 °C temperature
- Compact ROHS-compliant 4 mm x 4 mm QFN Package

APPLICATIONS

- Voice over IP telephones
- · Wireless access points
- · Security and surveillance IP cameras
- · Point-of-sale terminals
- · Internet appliances
- Network devices

1. Ordering Guide

Table 1.1. Si3404 Ordering Guide

Ordering Part Number	Package	Temperature Range (Ambient)	Applications
Si3404-A-GM	4 x 4 mm 20-QFN Pb-free, RoHS-compliant	–40 to 85 °C Extended	All Purposes

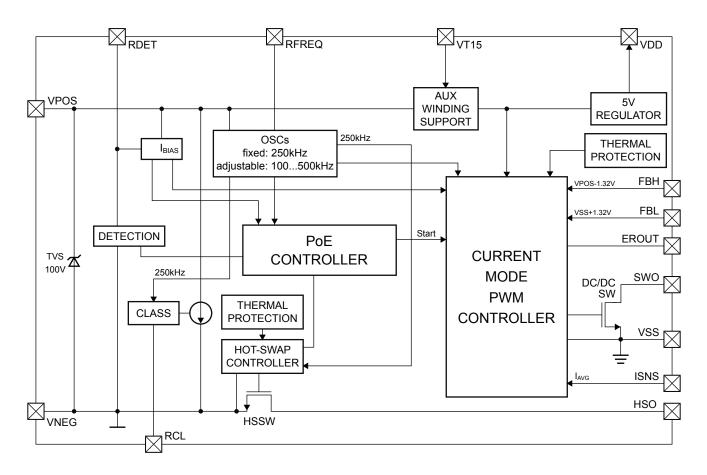
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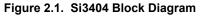
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2. System Overview

The following Block Diagrams will give the designer a sense for the internal arrangement of functional blocks, plus their relationships to external pins. The Block Diagrams are followed by a description of the features of these integrated circuits.

2.1 Block Diagram





2.2 Power over Ethernet (PoE) Line-Side Interface

The PoE line interface consists of external diode bridges, internal surge protection, and protocol interface support for detection and classification.

The chip features active protection against surge transients and accidentally applied telephony voltages.

2.2.1 Surge Protection

The surge protection circuit is activated if the VPOS-VNEG voltage exceeds T_{PROT} and the hotswap switch is off (dc-dc is not powered). If the hotswap switch is on, the surge power is sunk in the dc-dc's input capacitance.

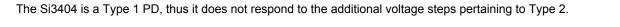
The internal surge protection can be overridden with an external TVS if higher than specified surge conditions need be tolerated. The external surge device must be connected in parallel to the internal one; therefore, the designer must ensure that the external surge protection will activate prior to the internal surge protection.

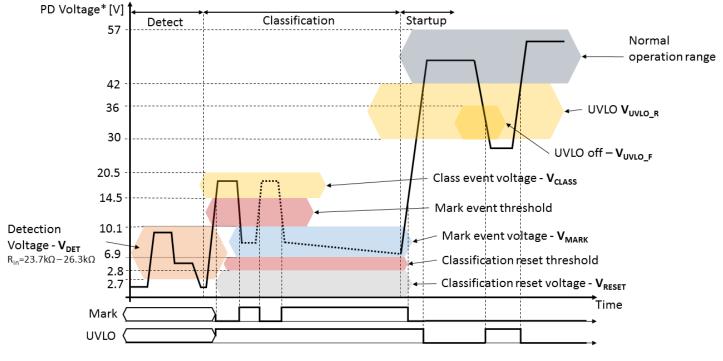
2.2.2 Telephony Protection

The Si3404 provides protection against telephony ringing voltage. The telephony ringing is much longer than the surge pulse but it has less energy, therefore, the Si3404 has a switch parallel with the supply (VPOS and VNEG). When the protection circuit is activated, it turns ON the telephony switch; the ringing energy then dissipates on this switch and ringing generator resistance (> 400 Ω).

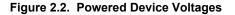
2.2.3 Detection and Classification

When the Si3404 is connected via Ethernet cable to a PSE-enabled Ethernet switch, it has to provide a characteristic resistance (\sim 25 k Ω) to the PSE in a given voltage range (2.7–10.1 V). This is called detection. After the PSE detects the PD, the PSE increases the voltage above the classification threshold 14.5 V. Then, the PD provides the classification current to inform the PSE about its required power class (Class 1, 2, 3, or 4). Type 1 PSEs cannot provide enough power for a Class 4 PD. Type 2 PSEs have additional voltage steps before switching on the PD. After an initial classification voltage pulse, the Type 2 PSE reduces the voltage below the mark threshold level (10 V) then raises it up again to the Class event range. Last, before switching ON the DCDC it reduces the voltage again.





*Voltages shown are representative. Refer to Electrical Characteristics table.



2.3 Hotswap Switch

The internal hotswap switch (HSSW) is turned on (conducting) when the PoE interface voltage goes above V_{UVLO_R} . It provides limited inrush current until the dcdc side capacitor is charged. The hotswap switch turns off (open) if voltage on the HSSW switch is greater than $V_{HSSW OFF}$.

In overload, the hotswap switch goes into current-limiting mode with a current limit of I_{OVL} . It will turn back ON after $T_{WAITHSSW}$ elapses and the dc-dc input capacitor is recharged, meaning the HSO-VNEG voltage is less than V_{HSSW} ON.

2.4 HSSW State Machine

The HSSW operates as simple 4-state state machine:

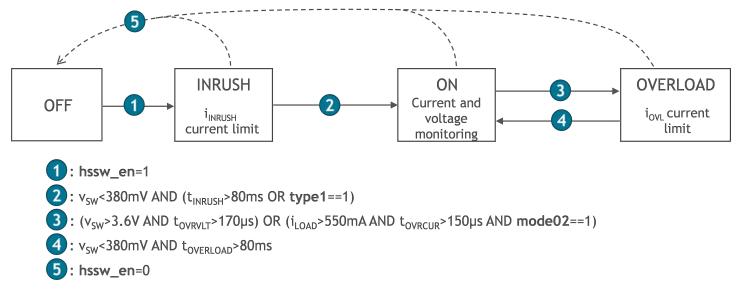


Figure 2.3. Hotswap Switch 4-State Machine

Note: Internal signal names are shown in this Figure, not to be confused with external pin names. For the below discussion, I_{LOAD} is the switch current, and V_{HSSW} is the voltage drop of the switch. In other words, V_{HSSW} = HSO – VNEG. All the voltage, current and time limits of the above diagram are typical values.

OFF State

HSSW turn-on is controlled by UVLO, the undervoltage lockout feature. When UVLO is engaged, the HSSW is OFF. In this state, the HSSW is in idle mode, VNEG and HSO pins are disconnected. In normal operation, a complete detect/classification procedure precedes the HSSW turn-on, and the control of this sequence is implemented in the state machine logic of the chip.

INRUSH State

After the controller enables the HSSW, the block starts operation in the INRUSH state. In this state the switch itself is not directly turned on, but operating in a closed-loop current limit mode to avoid high current peaks during the charging of the primary bypass cap of the dc to dc converter.

If the V_{HSSW} voltage drops below 380 mV (meaning the bypass cap is 99% charged), the HSSW will change state to ON.

ON State

In ON state, the HSSW switch is directly turned on. The HSSW circuit continuously monitors V_{HSSW} . HSSW will change to OVERLOAD state if V_{HSSW} voltage increases over 3.6 V for at least 140 μ s.

OVERLOAD State

In OVERLOAD state the HSSW operates in closed-loop low current limit mode. If the V_{HSSW} voltage drops below 360 mV again, and the HSSW has been in the OVERLOAD state for at least 80 ms, the HSSW will change back to the ON state.

2.5 DC to DC Converter

The dc-to-dc converter is current-controlled for easier compensation and more robust protection of circuit magnetics. The controller has the following features:

- · High- and low-side feedback (supports buck and flyback topologies).
- <1 Ω internal switching FET
- Overcurrent detection
- Cycle skipping at low current and short circuit conditions

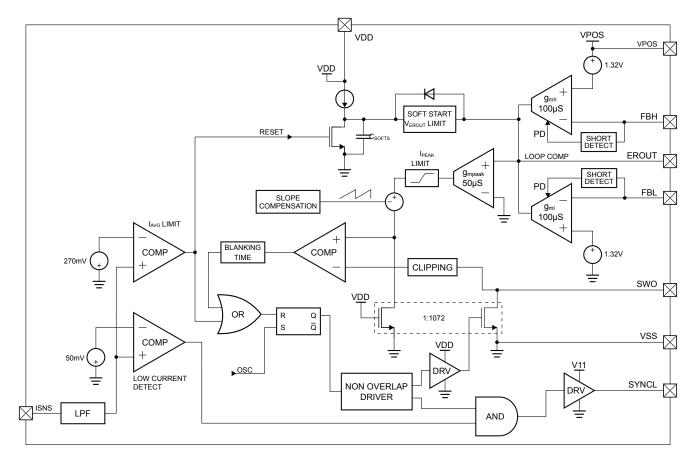


Figure 2.4. Si3404 DC-DC Converter

Feedback to the dcdc converter can be provided in three ways:

- · High side, referenced to VPOS, connected to FBH pin (buck converter)
- · Low side, referenced to VSS, connected to FBL pin (nonisolated flyback)
- Directly to EROUT pin by a voltage to current converter (isolated flyback)

The EROUT pin provides current output (if FBL or FBH is used) and voltage input. Also, the loop compensation impedance is connected to EROUT. The active voltage range is V_{EROUT}, which is proportional to the converter peak current.

The converter startup is not configurable; soft start is accomplished by internal circuitry. Soft start time is T_{SOFTSTART}. The intelligent soft start circuit dynamically adjusts the soft start time depending on the connected load.

2.5.1 Average Current Sensing, Overcurrent, and Low-Current Detection

The application average current is sensed by an external resistor (R_{SENSE}) connected between VSS and ISNS. Overcurrent is detected and triggered when the voltage on the sense resistor exceeds V_{ISNS_OVC} . Sizing the resistor allows the designer to set the overcurrent limit according to application needs. When overcurrent is triggered, the dcdc controller goes into reset until the overcurrent resolves. When the overcurrent is no longer present, the controller starts up again with softstart.

2.6 Tunable Oscillator

The dcdc frequency can be fixed to 250 kHz or tunable by an external resistor.

The tuning resistor must be connected between the R_{FREQ} pin and VPOS. If R_{FREQ} is shorted to VPOS, the fixed frequency oscillator will provide the clock, F_{OSCINT} , to the dcdc converter; otherwise, the resistor will determine the frequency as shown in the curve below.

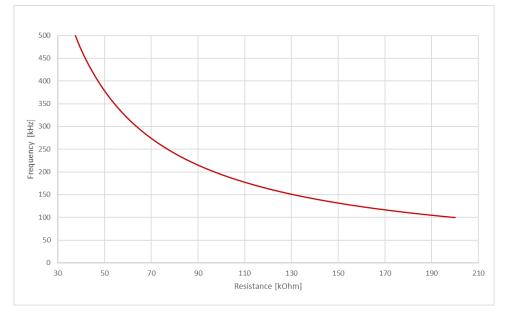


Figure 2.5. RFREQ Frequency Selector Diagram

2.7 Regulators

The chip provides a 5 V output to power LEDs or optocouplers. This is a closed-loop regulator, which ensures accurate output voltage. The 5 V regulator is supplied by an internal 11 V open loop regulator. The 11 V regulator is supplied by a coarse regulator, which is also open-loop. With the Si3404, the VT15 pin can be used to supply this regulator from an optional auxiliary transformer bias winding. The advantage of doing so is additional power saving. The application must be designed to ensure that the absolute maximum rating voltage for the VT15 pin is not exceeded.

2.8 External Wall Support

The Si3404 allows the use of a range of external wall adapters as a primary or secondary supply. For details on adapter connection, please refer to "AN1130: Using the Si3406/Si34061/Si34062 PoE+ and Si3404 PoE PD Controller In Isolated and Non-Isolated Designs".

3. Application Examples

The following diagrams demonstrate the ease of use and straightforward BOM of the Si3404 Powered Device IC. Detailed reference designs are available in Evaluation KIT User Guides. Also refer to "AN1130: Using the Si3406/Si34061/Si34062 PoE+ and Si3404 PoE PD Controller In Isolated and Non-Isolated Designs".

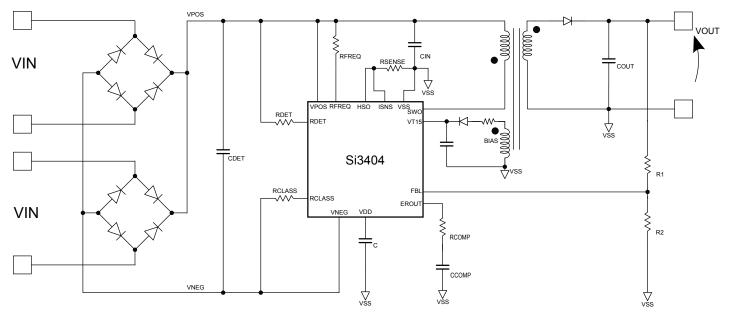
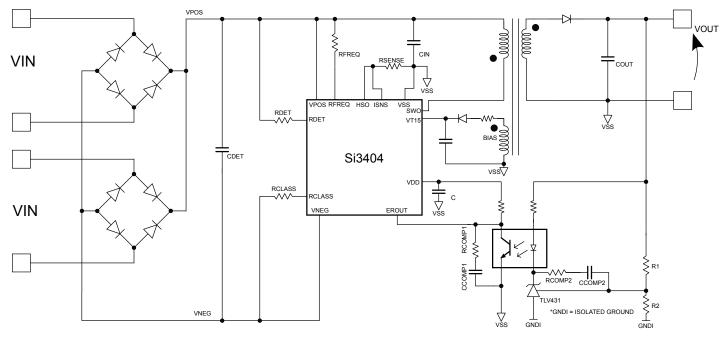
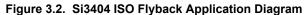


Figure 3.1. Si3404 Non-ISO Flyback Application Diagram





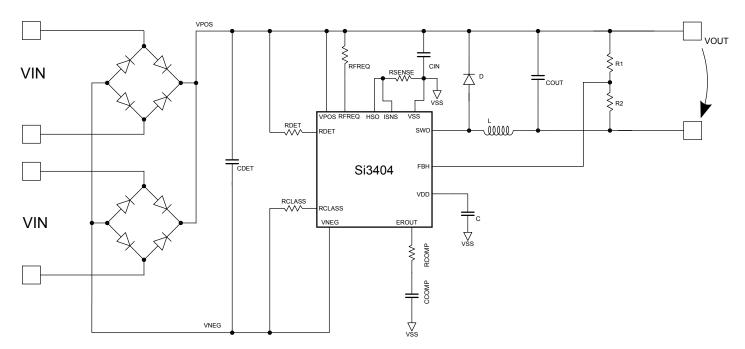


Figure 3.3. Si3404 Buck Application Diagram

4. Electrical Specifications

Туре	Description	Min	Мах	Units
	VNEG-VSS, VPOS- VNEG, HSO ² , RDET ³	-0.7	100	V
	SWO-VSS	-0.7	120	V
Voltage	ISNS	-1	1	V
Voldge	Low Voltage pins: FBH ³ , EROUT, FBL, RCL ² , RFREQ ³	-0.7	6	V
	Mid Voltage pins: VT15	-0.7	18	V
Peak Current VPOS		–TBD	TBD	A
Temperature	Storage Temperature	-65	150	Э°
	Ambient Operating Temperature	-40	85	

Table 4.1. Absolute Maximum Ratings¹

Note:

1. Unless otherwise noted, all voltages referenced to VSS. Permanent device damage may occur if the maximum ratings are exceeded. Functional operation should be restricted to those conditions specified in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may adversely affect device reliability.

2. Voltage referenced to VNEG.

3. Voltage referenced to VPOS.

Symbol	Parameter (Condition)	Min	Тур	Мах	Unit
V _{PORT}	VPORT = VPOS – VNEG	1.5	_	57	V
V _{HV_OP}	VNEG-VSS, VNEG-HSO, VPOS- VSS	1.5	_	57	V
V _{LV_OP}	VPOS referred low voltage pins: RFREQ, RDET, FBH	-5.5	_	0	V
V _{LV_OP}	VSS referred low voltage pins: VDD, FBL, EROUT	0	_	5.5	V
V _{ISNS_OP}	VSS referred current sensing pin: ISNS	-0.5	_	0.5	V
V _{LV_OP}	VNEG referred low voltage pins: RCL	0	_	5.5	V
V _{MV_VT15}	VSS referred medium voltage pin VT15 ¹	12	14.5	16.5	V
I _{AVG}	Allowable continuous current on SWO, VSS, HSO, VNEG	_	_	600	mA
I _{PEAK} Peak current on SWO, VSS, HSO, VNEG Max 75 ms 5% Duty Cycle		_	_	683	mA

Table 4.2. Recommended Operating Conditions

1. V_{MV_VT15} is relevant for Si3404 only when an external auxiliary bias winding from the primary side of the transformer is being used to improve power conversion efficiency. This can be left undriven, in which case an internal regulator will be used.

Symbol	Parameter (Condition)	Min	Тур	Max	Unit
PoE PROTOCOL					
Detection					
V _{DET}	Detection Voltage (at V _{PORT})	1.5	_	8.9	V
Classification					
V _{RESET}	Classification Reset (at V _{PORT})	0	_	1.61	V
V _{CLASS}	Classification Voltage (at V _{PORT})	13.4	_	21.4	V
	Class 0 (R _{CLASS} > 681 Ω)	0	_	4	mA
	Class 1 (R _{CLASS} = 140 Ω @ 1%)	9	_	12	mA
I _{PortCLASS}	Class 2 (R _{CLASS} = 75 Ω @ 1%)	17	_	20	mA
	Class 3 (R _{CLASS} = 48.7 Ω @ 1%)	26	_	30	mA
Power On and U	VLO				
V _{UVLO_R}	Hotswap closed and converter on	_	37	_	V
V _{UVLO_F}	Hotswap open and converter off	_	32	_	V
Thermal Charact	teristics				
T _{shd}	Thermal shutdown	_	160	_	°C
T _{HYST}	Thermal shutdown hysteresis	_	20	_	°C
On-Chip Transie	nt Voltage Suppression/Protection				
T _{PROT}	TVS protection activation voltage (VPOS-VNEG)	100	_	_	V
Hotswap Switch					
l _{inrush}	Inrush current	100	170	200	mA
IMAXHSSW	Maximum continuous operating cur- rent	_	_	600	mA
V _{HSSW_ON}	Switch ON voltage	_	380	_	mV
V _{HSSW_OFF}	Switch OFF voltage, HSSW goes to overload cycle	_	3.5	_	V
I _{OVL}	Switch current limit in OVERLOAD State	8.7	10.5	12.4	mA
TWAITHSSW	Wait time in OVERLOAD	80	96	116	ms
R _{ONHSSW} Internal hotswap drain-source resist- ance while ON		0.65	1.5	2.9	Ω
DC-DC	1		1	1	1
ISWOPEAK	Peak current limit of internal FET (SWO pin)	2.1	_	2.7	A
FOSCINT	Using internal Oscillator	_	250	_	kHz
F _{OSCEXT}	Using external Oscillator, tunable on pin RFREQ	100	_	500	kHz

Table 4.3. Electrical Characteristics

Symbol	Parameter (Condition)	Min	Тур	Max	Unit
DUC	Output duty cycle of PWM	_	TBD	75	%
V _{FBREF}	FBH (referenced to VPOS) and FBL (referenced to VSS) reference volt- age	_	1.32	_	v
V _{EROUT}	Operating voltage range of error in- put	1	_	4	V
V _{ISNS_OVC}	Overcurrent limit voltage on ISNS (ref. to VSS)	_	-270	_	mV
T _{SOFTSTART}	Startup time	_	4	—	ms
R _{ONDCDC}	Internal DCDC switching FET drain- source resistance while ON	_	0.9	1.2	Ω
Regulators	· · · · · · · · · · · · · · · · · · ·				
VT15	Override internal regulator with transformer winding	13	_	16.5	V
VDD	5 V regulated output	4.85	5.1	5.46	V
VDD _{ILIM}	DC current limit of VDD	9.7	11.2 12.9		mA
C _{REG}	C _{REG} Filter capacitor on VDD		100	—	nF
Power Dissipation	on l		1		
PINTMAX	DC-DC max power internal FET	_	1.2	1.5	W
P _{MAX}	Total chip power	_	TBD	TBD	W
I _{PortOP}	I _{PortOP} Operating current (V _{PORT} 57 V; 250 kHz)		3	4	mA
Package Therma	I Characteristics		1	1	1
	θ _{JA-EFF} QFN20 ¹		46.8	_	C°/W

5. Pin Descriptions

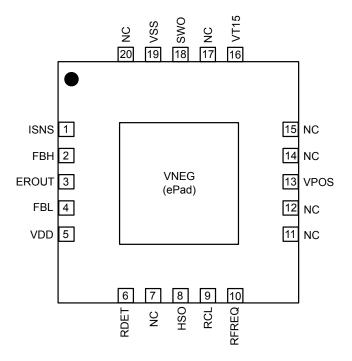


Figure 5.1. Si3404 Pinout

Table 5.1. Pin Descriptions

Si3404 Pins	Name	Ref	Dir.	Vrange	Description
1	ISNS	VSS	I	-0.5 to 0	Chip current sense resistor input
2	FBH	VPOS	I	0–5	High side (VPOS referred) dcdc feedback (buck converter)
3	EROUT	VSS	Ю	0–5	Error amplifier current output, compensation impedance input
4	FBL	VSS	I	0–5	Low side (ground referenced) dcdc feedback (flyback con- verter)
5	VDD	VSS	0	0–5	5V regulator output
6	RDET	VPOS	IO	0–100	Detection resistor
8	HSO	VNEG	IO	0–100	Hot swap switch output
9	RCL	VNEG	IO	0–5	Classification resistor
10	RFREQ	VPOS	IO	0–5	Oscillator frequency tuning resistor, tie to VPOS to select default freq
13	VPOS	_	IO	0–100	Rectified high-voltage supply positive rail
16	VT15	VSS	I	0–16.5	Dcdc transformer auxiliary winding input
18	SWO	VSS	0	0–120	Internal dcdc switch output (NMOS drain)
19	VSS	_	IO	0	Dcdc converter primary ground
ePad	VNEG	_	IO	0	Rectified high voltage supply ground
7, 11, 12, 14, 15, 17, 20	NC			_	Do not connect

5.1 Detailed Pin Descriptions

Pin Name	Detailed Description	Circuit Detail
ISNS	Average current sense resistor input. The resistor value will set the maxi- mum allowed current for the application. The overcurrent threshold voltage V _{ISNS_OVC} . Note that this pin voltage goes below VSS.	VSS VSS VSS VSS
FBH	High side dcdc feedback input. Need to be tied to VPOS when not used. See VFBREF.	VPOS FBH
EROUT	dcdc converter error output; current out, voltage sense. Loop compensating impedance should be connected here. I _{EROUT} = (V _{FBH} – V _{FBREF}) x 50 μA or I _{EROUT} = (V _{FBL} – V _{FBREF}) x 50 μA	VDD VDD EROUT VSS
FBL	Low side dcdc feedback input. Need to be tied to VSS when not used. See $V_{\mbox{FBREF}}$	VDD FBL VSS
VDD	Regulated 5 V relative to VSS. There is no foldback characteristic, reaching VDD _{ILIM} the output voltage decreases. The regulator needs C_{REG} external capacitance.	VDD VDD VSS

Table 5.2. Circuit Equivalent and Description of Die Pads

Pin Name	Detailed Description	Circuit Detail
RCL	Classification resistor input. For class 0 this pin can be left floating. Pin is active only at time of classification.	+ Rext NNEG
RFREQ	Used for adjusting the oscillator frequency. The frequency is inversely proportional to the value of the connected resis- tor.	Rexternal Freq
VPOS, VNEG	Main chip input power. Note that VNEG (the ePad on the bottom of the chip) also provides thermal relief.	VPOS CT1,CT2 SP1,SP2
HSO	Hotswap Switch Output. The switch shorts the VNEG and HSO pins, and in- cludes several other functions. See hotswap switch section for details.	HSO 120V VNEG
RDET	The user has to tie the RDET resistor between this pin and VPOS. During detection, a high voltage switch pulls down RDET to VNEG. After detection, the reference block uses RDET as absolute chip current reference, forcing -750 mV relative to VPOS, creating 30 μ A for the internal blocks.	120V 120V RDET 120V VNEG

Pin Name	Detailed Description	Circuit Detail
VT15	VT15 is input for an optional 15 V supply generated by an auxiliary trans- former bias winding. If the bias winding voltage is lower than VT15, the in- ternal 15 V coarse regulator will provide the current for the 11 V regulator.	VPOS
SWO	Dcdc converter switching transistor drain output, Vmax = 120 V.	Swo
VSS	DC-DC converter ground.	L20V ESD clamp VSS

6. Packaging

6.1 Package Outline: Si3404

The figure below illustrates the package details for the Si3404. The table lists the values for the dimensions shown in the illustration.

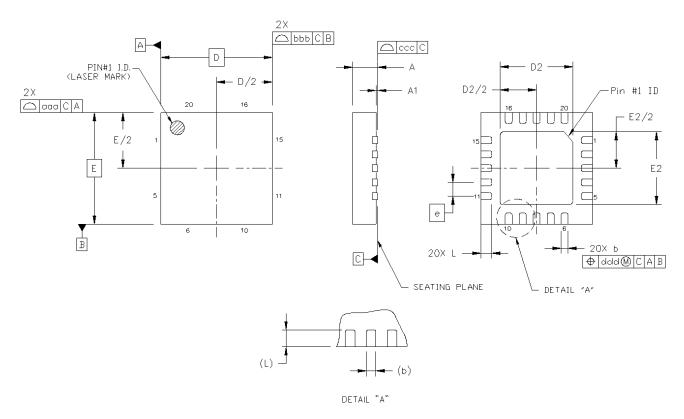


Figure 6.1. 20-Pin, QFN Package

Dimension	Min	Nom	Мах		
A	0.80	0.85	0.90		
A1	0.00	0.02	0.05		
b	0.18	0.25	0.30		
D		4.00 BSC.			
D2	2.55	2.60	2.65		
e	0.50 BSC.				
E	4.00 BSC.				
E2	2.50	2.60	2.70		
L	0.30	0.40	0.50		
ааа	_	_	0.10		
bbb			0.10		
CCC	— — 0.08				
ddd	_	_	0.10		
eee	_	—	0.10		

Si3404 Data Sheet Packaging

Dimension	Min	Nom	Мах		
Note:					
1. All dimensions shown are in millimeters (mm) unless otherwise noted.					
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.					
3. This drawing conforms to the JEDEC Solid State Outline MO-220, Variation VGGD-8.					
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.					

6.2 Land Pattern: Si3404

The figure below illustrates the land pattern details for the Si3404. The table lists the values for the dimensions shown in the illustration.

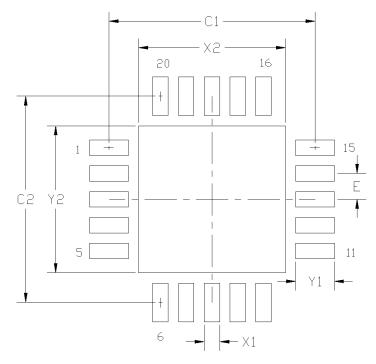


Figure 6.2. 20-Pin, QFN Land Pattern

Table 6.2. Land Pattern Dimer	nsions
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Dimension	Min	Мах
C1	3.90	4.00
C2	3.90	4.00
E	0.50 BSC	
X1	0.20	0.30
X2	2.55	2.65
Y1	0.65	0.75
Y2	2.55	2.65

Si3404 Data Sheet	
Packaging	

Dimension	Min	Мах	
Note:			
General			
1. All dimensions shown are in millimeters (mm) unless otherwise noted.			
2. This land pattern design is based on the IPC-7351 guidelines.			
Solder Mask Design			
1. All metal pads are to be non-solder mas minimum, all the way around the pad.	< defined (NSMD). Clearance between the so	older mask and the metal pad is to be 60 mm	
Stencil Design			
1. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release			
2. The stencil thickness should be 0.125 mm (5 mils).			
3. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads.			
4. A 2x2 array of 1.10 mm x 1.10 mm openings on 1.30 mm pitch should be used for the center ground pad.			
Card Assembly			
1. A No-Clean, Type-3 solder paste is recommended.			

2. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

7. Si3404 Top Marking

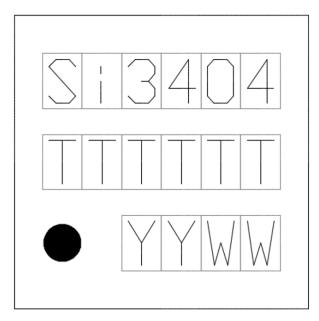


Figure 7.1. Si3404 Top Marking

Table 7.1. Si3404 Top Marking Explanation

Mark Method:	Laser	
Pin 1 Mark:	Circle = 0.50 mm Diameter (Lower-Left Corner)	
Font Size:	0.6 Point (24 mils)	
Line 1 Mark Format:	Device Part Number	Si3404
Line 2 Mark Format:	ТТТТТТ	Trace code (assigned by the assembly subcontractor)
Line 3 Mark Format:	YY = Year	Assembly Year
	WW = Work Week	Assembly Week

8. Revision History

Revision 0.5

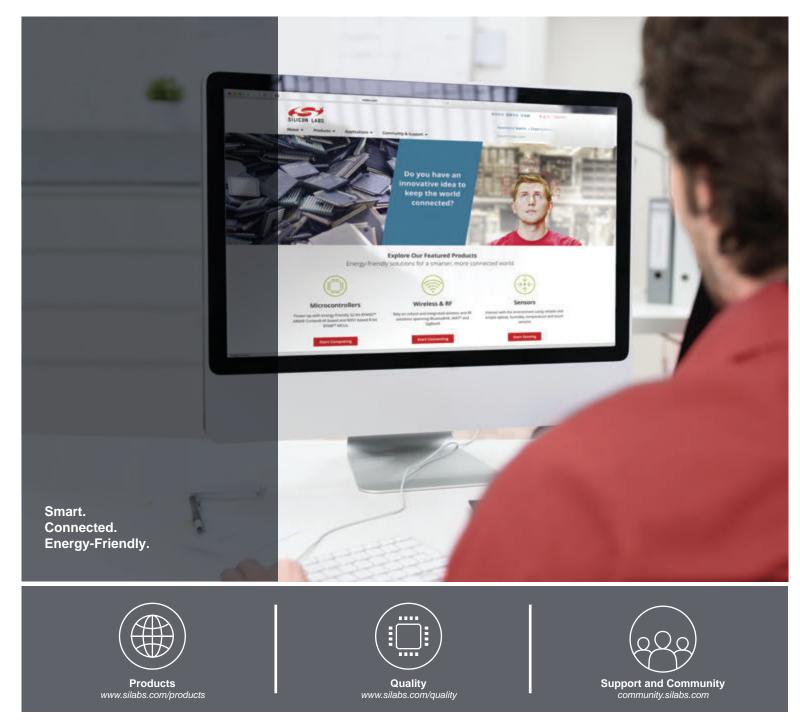
February, 2018

- Updated 2. System Overview and 3. Application Examples.
 - Added theory of operation and application content.
- Updated Table 4.1 Absolute Maximum Ratings¹ on page 11, Table 4.2 Recommended Operating Conditions on page 12, and Table 4.3 Electrical Characteristics on page 13.
 - Clarified multiple parameters.
- Added 5.1 Detailed Pin Descriptions.
- Added 6. Packaging including outline and land pattern.

Revision 0.1

March, 2017

· Initial release.



Disclaimer

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